Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

HS1205

APPLICATIONS

Large Current Switching

ABSOLUTE MAXIMUM RATINGS（T_a=25℃）

T_{stg}——Storage Temperature…… −55~150℃

T_j——Junction Temperature…… 150℃

P_C——Collector Dissipation（T_c=25℃）…… 10W

P_C——Collector Dissipation（T_A=25℃）…… 1W

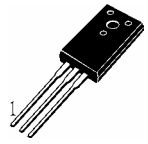
V_{CBO}——Collector-Base Voltage…… -25V

V_{CEO}——Collector-Emitter Voltage…… -20V

V_{EBO}——Emitter-Base Voltage…… -5V

I_C——Collector Current……-5A

TO-126



1－Base，B
2－Collector，C
3－Emitter，E

ELECTRICAL CHARACTERISTICS（T_a=25℃）

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	−25			V	I_C=-10μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	−20			V	I_C=-1mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	−5			V	I_E=-10μA, I_C=0
I_{CBO}	Collector Cut-off Current			−500	nA	V_{CB}=-20V, I_E=0
I_{EBO}	Emitter Cut-off Current			−500	nA	V_{EB}=-4V, I_C=0
H_{FE}（1）	DC Current Gain	100		400		V_{CE}=-2V, I_C=-500mA
H_{FE}（2）	DC Current Gain	60				V_{CE}=-2V, I_C=-4A
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage		−250	−500	mV	I_C=-3A, I_B=-60mA
$V_{CE(sat2)}$	Collector- Emitter Saturation Voltage		−1.0	−1.3	V	I_C=-3A, I_B=-60mA
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		−0.94	−1.2	V	I_C=-3A, I_B=-60mA
ft	Current Gain-Bandwidth Product		320		MHz	V_{CE}=-5V, I_C=-200mA,
Cob	Output Capacitance		60		pF	V_{CB}=-10V, I_E=0， f=1MHz
t_{ON}	Turn-On Time			40	nS	See specified test circuit
t_{STG}	Storage Time			200	nS	
t_F	Fall Time			10	nS	

h_{FE} Classification

R	S	T
100—200	140—280	200—400